

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Application Number	10/575,625
	Confirmation Number	4644
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	First Named Inventor	Hiromitsu SAKAI
	Art Unit	2811
	Examiner Name	Shouxiang HU
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	5.	C. ADELMANN, ET AL: "Atomic-layer epitaxy of GaN quantum wells and quantum dots on (0001) AlN", JOURNAL OF APPLIED PHYSICS, AMERICAN INSTITUTE OF PHYSICS, NEW YORK, US LNKD- DOI:10.1063/1.1458049, vol. 91, no. 8, 15 April 2002 (2002-04-15), pages 5498-5500, XP012056297 ISSN: 0021-8979 * page 5498, column 2, lines 7-9 ** page 5499, column 1, lines 14-28; figure 1b ** page 5499, column 2, line 26 - page 5500, column 1, line 9; figures 3a,b ** page 5500, column 2, lines 6-8, 13, 14 *	
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